S.E (ELECTROMICS (BJO. MEDICAL) (SEM 11) (REV)

1=1 ectronic Circuit AMIysis Design1

Con. 2501-07.

432: 1stHf07

(REVISED COURSE)

ND-425

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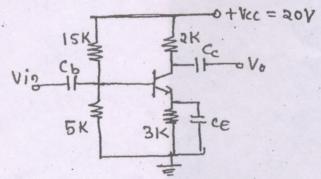
29th aug 2007

(3 Hours)

[Total Marks: 100

N.B. (1) Question No. 1 is compulsory.

- (2) Solve any four from remaining questions.
- (3) Assume suitable data if necessary.
- (a) Compare BJT and FET amplifiers.
 - b) Determine I_{CBO} at 75° if it has a value of 10 μA at 30°C.
- (c) What is the role of circuit resistance R in clipping circuits. Find its value if the diode used ? in clipper has forward resistance of 50 Ω and reverse resistance of 10 M Ω .
- (d) Why CE configuration is preferred over CB and CC, when used as a switch.
- 2. (a) Draw a circuit diagram of a full wave rectifier with π filter. Derive expressions for ripple 10 factor. Explain the basic rectifier operation.
 - (b) For CE amplifier derive the expressions for A_V, A_I, Z_i and Z_o.
- 3. (a) Determine the Q print and draw the dc load line for the circuit shown below:—

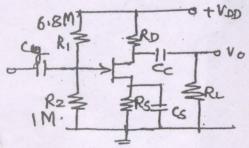


(b) For the circuit shown below determine A_V, Z_i and Z_o.

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$$\begin{aligned} &V_{DD}=20V\\ &R_D=1.5K^-\\ &R_s=1~K~\Omega\\ &R_L=10~K~\Omega \end{aligned}$$

$$I_{DSS} = 10 \text{ mA}$$

 $V_{as(OFF)} = V_p = 3 \text{ V}$
 $r_d = 50 \text{ K } \Omega$
 $I_{DQ} = 3.8 \text{ mA}$

- 4. (a) Design a single stage RC coupled CE amplifier to meet the following specification. $V_O = 2 \text{ V}, A_V \ge 70, S \le 10, \text{ Audio frequency range. } R_L \simeq 10 \text{ K}\Omega. \text{ Use BJT BC 147A.}$
 - (b) For above designed circuit determine maximum expected voltage gain Z_i and Z_o.

5. Design a single stage RC coupled CS amplifier to meet the following specifications:— 20

$$f_L = 20 \text{ Hz}$$
 $V_O = 2 \text{ V}$
 $I_D = 3.3 \pm 0.6 \text{ mA}$
 $I A_V I = 11$
 $BW = 11 \text{ (FET Type)}$

Calculate R_i, R_o and V_{o max} for the designed amplifier.

6. (a) What is clipping? Explain. How a diode circuit can be used for single level and double level clipping?
(b) Compare EMOSFET and DMOSFET on basis of their construction, working principle, characteristics and biasing circuits.

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- 7. Write short notes on any three :-
 - (a) Thermal stabilization and compensation
 - (b) Photo diode
 - (c) Condition for zero temp. drift in FET
 - (d) Avalanche and zener breakdown mechanism
 - (e) Hybrid π equivalent circuit of BJT.